

2SC4102 / 2SC3906K / 2SC2389S

- 1) High breakdown voltage. ($BV_{CEO} = 120V$)
- 2) Complements the 2SA1579 / 2SA1514K / 2SA1038S.

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CB0}	120	V
Collector-emitter voltage	V_{CE0}	120	V
Emitter-base voltage	V_{EB0}	5	V
Collector current	I_C	50	mA
Collector power dissipation	2SC4102 / 2SC3906K	0.2	W
	2SC2389S	0.3	
Junction temperature	T_J	150	°C
Storage temperature	T_{ST0}	-55~+150	°C

Type	2SC4102	2SC3906K	2SC2389S
Package	UMT3	SMT3	SPT
hfe	RS	RS	RS
Marking	T*	T*	—
Code	T106	T146	TP
Basic ordering unit (pieces)	3000	3000	5000

*Donator by

Each lead has same dimensions

ROHM : UMT3 (1) Emitter
EIAJ : SC-70 (2) Base
JEDEC : SOT-323 (3) Collector

Technical drawing of a 3-lead resistor. The top view shows a rectangular body with a width of 1.6 and a total length of 2.8. The distance from the left edge to the first lead is 0.4. The distance between the first and second leads is 0.95, and the distance between the second and third leads is 1.9. The total width of the leads is 1.9. The side view shows a height of 0.15, a lead height of 0.8, and a lead width of 0.3. The distance from the left edge to the first lead is 0.3 min. The distance between the first and second leads is 0.1. The distance between the second and third leads is 0.1. The total length of the resistor is 1.1. Each lead has the same dimensions.

ROHM : SMT3
EIAJ : SC-59
JEDEC : SOT-346

(1) Emitter
(2) Base
(3) Collector

ROHM : SPT
EIAJ : SC-72

(1) Emitter
(2) Collector
(3) Base

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	120	–	–	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	120	–	–	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	5	–	–	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	–	–	0.5	μA	$V_{CB}=100V$
Emitter cutoff current	I_{EBO}	–	–	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	0.5	V	$I_C/I_E=10mA/1mA$
DC current transfer ratio	h_{FE}	180	–	560	–	$V_{CE}=6V, I_C=2mA$
Transition frequency	f_T	–	140	–	MHz	$V_{CE}=12V, I_E=-2mA, f=100MHz$
Output capacitance	C_{ob}	–	2.5	–	pF	$V_{CB}=12V, I_C=0A, f=1MHz$